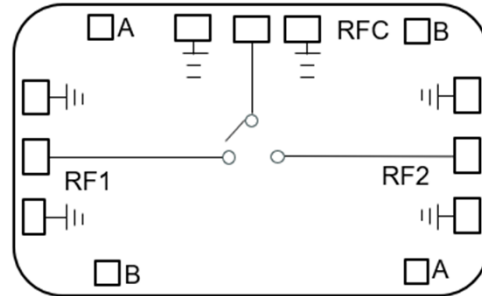


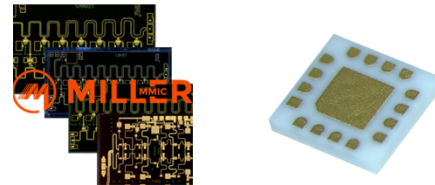
Features

- SP2T Reflective design
- Frequency:DC~4GHz
- Isolation: 55dB
- Insertion Loss: 0.5dB
- Return Loss (ON):15dB
- Control Voltage:0/-5V
- Switching Speed: 15 ns
- Die Size: 1.10 x 0.92 x 0.1 mm


Typical Applications

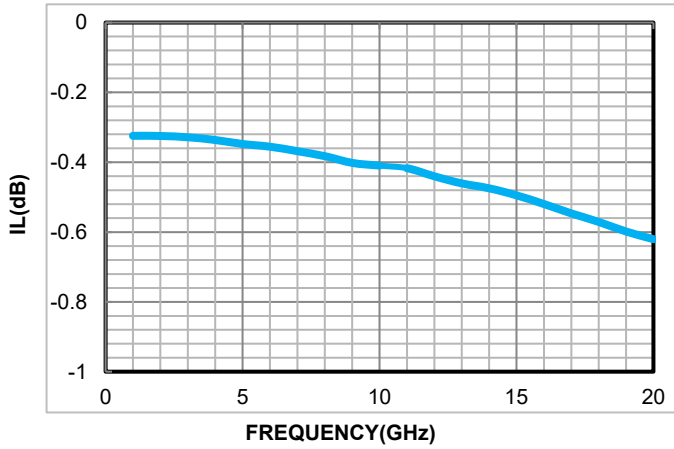
- Voltage control no current
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Customization available upon request

- QFN package available 3x3 mm

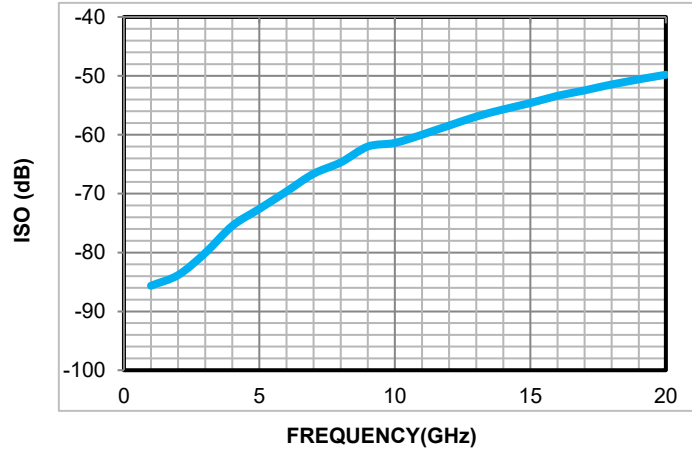

Electrical Specifications
TA = +25°C, VCTL=0/-5V

Parameters	Min.	Typ.	Max.	Units
Frequency	DC~4			GHz
Insertion Loss		0.5	0.8	dB
Isolation	45	55		dB
Return Loss (ON State)	13	20		dB
Input P-1		27		dBm
RF Input power			30	dBm
IIP3		32		dBm
Switching Speed	15			ns

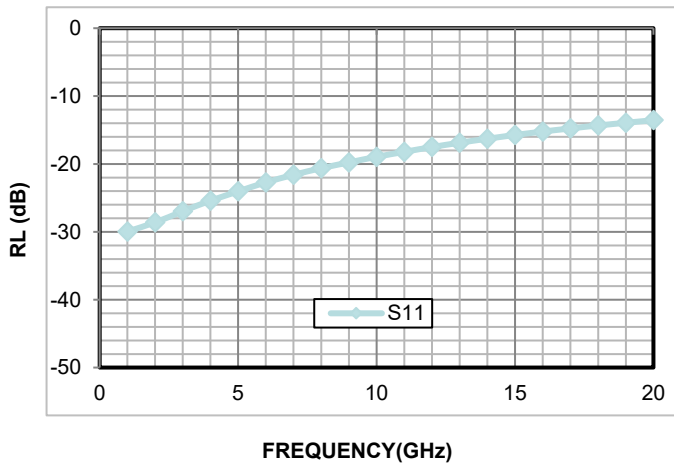
Insertion Loss vs. Frequency



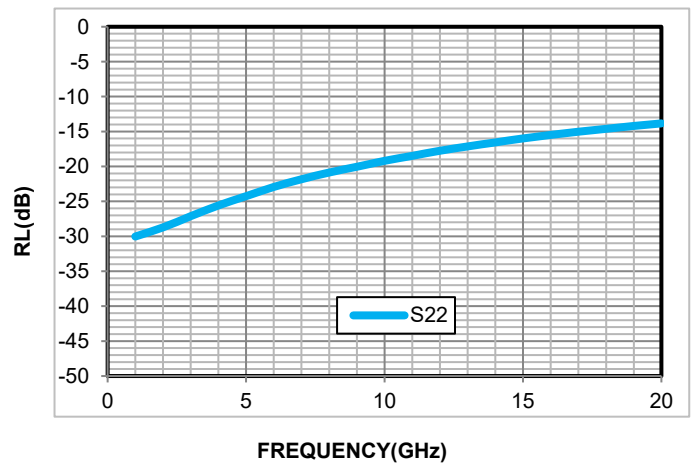
Isolation vs. Frequency



Input RL-On vs. Frequency



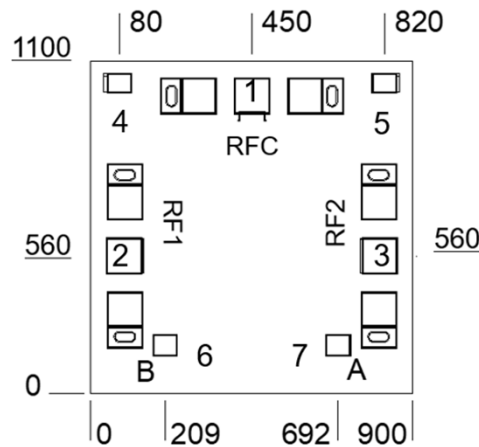
Output RL-On vs. Frequency





Outline Drawing:

All Dimensions in mm



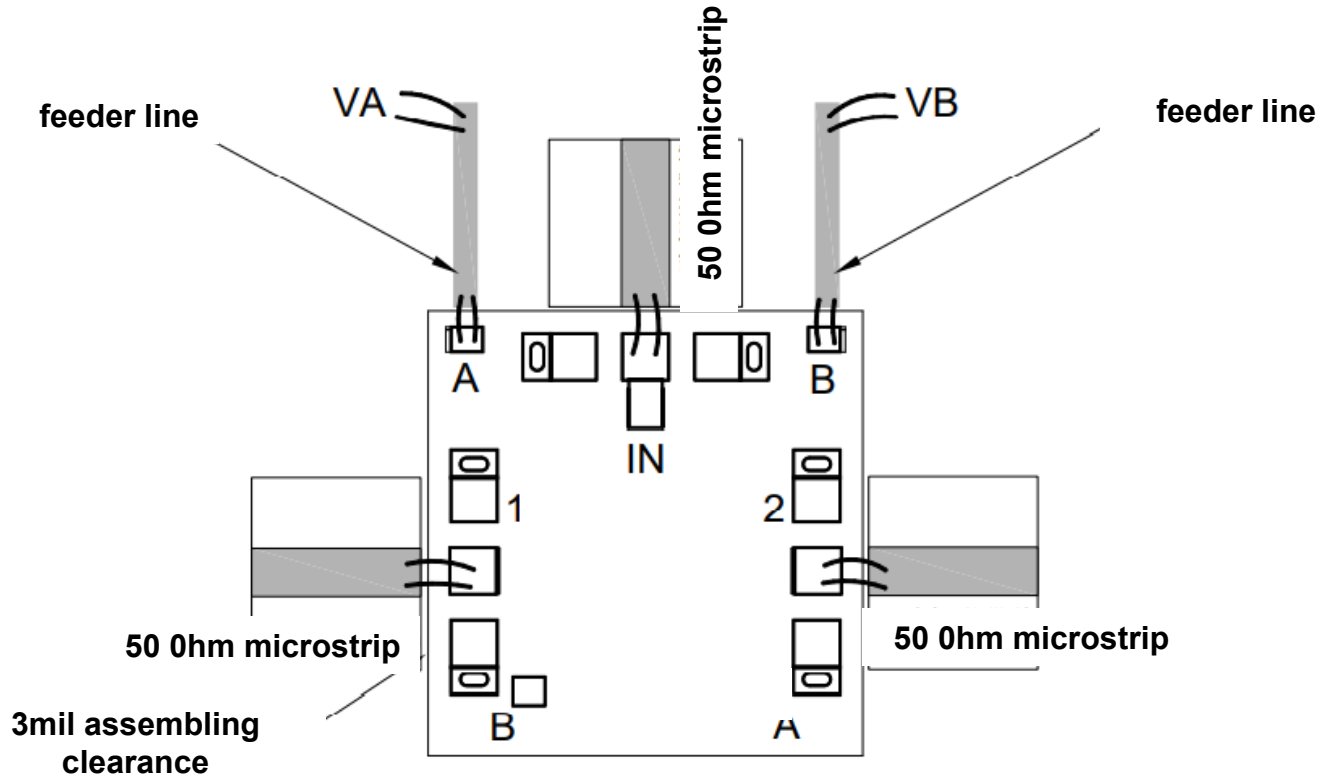
True Table

Vctrl (V)		Status	
A	B	RFC-RF1	RFC-RF2
-5	0	ON	OFF
0	-5	OFF	ON

Pad	Function	Description
1,2,3	IN, OUT	50 ohm circuit matched, and there is no blocking capacitor integrated inside the chip
4,5,6,7	VS	Control Voltage
Bottom of chip	GND	The bottom of the chip should be in good contact with the RF and DC ground



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +30dBm
2. Control Voltage: -8~+1V
3. Storage temperature: -65°C to +150°C
4. Operating temperature: -55°C to 125°C